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**IN THE SPECIFICATION**

Please amend the paragraph beginning on page 4, line 1, as follows:

The structure shown in Figure 1 may be exposed to a mild oxidant, such as hydrogen peroxide or  $R_2O_2$  (where R is an organic material),  $O_3$  in vapor or gas form, or  $O_2$  in gaseous form. The oxidation converts the germanide or silicide 16 into the germinate or silicate 16a as indicated in Figure 2. Next, the germinate or silicate 16a may be selectively etched using a non-destructive, low pH wet etchant, such as  $H_3PO_4$ , sulfuric acid, chelating species, or supercritical carbon dioxide at lower temperatures such as 25 to 120°C. In one embodiment, the wafers may be immersed in a bath of liquid etchant. These etchants have high selectivity and work by dissolution. This results in the selective removal of the silicide silicate 16a.